2SD1273, 2SD1273A

Silicon NPN triple diffusion planar type

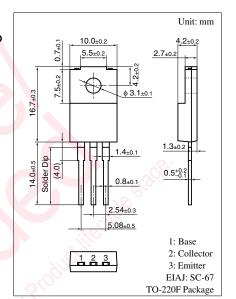
For power amplification with high forward current transfer ratio Complementary to 2SB1299

■ Features

- High forward current transfer ratio h_{FE}
- Satisfactory linearity of forward current transfer ratio h_{FE}
- Full-pack package which can be installed to the heat sink with one screw

■ Absolute Maximum Ratings $T_C = 25^{\circ}C$

| Parameter | | Symbol | Rating | Unit |
|-------------------------|---------------------|------------------|-------------|-------|
| Collector to base | 2SD1273 | V _{CBO} | 80 | V |
| voltage | 2SD1273A | | 100 | |
| Collector to | 2SD1273 | V _{CEO} | 60 | V |
| emitter voltage | 2SD1273A | | 80 | |
| Emitter to base voltage | | $V_{\rm EBO}$ | 6 | V |
| Peak collector current | | I_{CP} | 6 | A |
| Collector current | | I_{C} | 3 | A |
| Base current | | I_{B} | 1 | A |
| Collector power | $T_C = 25^{\circ}C$ | P _C | 40 | w |
| dissipation | $T_a = 25^{\circ}C$ | | 2 | |
| Junction temperature | | T _j | 150 | %C √6 |
| Storage temperature | | T_{stg} | -55 to +150 | °C |
| | | | 11 710 | |



■ Electrical Characteristics T_C = 25°C

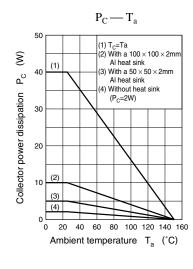
| Paramete | r col | Symbol | Conditions | Min | Тур | Max | Unit |
|---|------------|----------------------|--|-----|-----|-------|------|
| Collector cutoff | 2SD1273 | I_{CBO} | $V_{CB} = 80 \text{ V}, I_{E} = 0$ | | | 100 | μΑ |
| current | 2SD1273A | | $V_{CB} = 100 \text{ V}, I_{E} = 0$ | | | 100 | |
| Collector cutoff curren | t | I _{CEO} | $V_{CE} = 40 \text{ V}, I_{B} = 0$ | | | 100 | μΑ |
| Emitter cutoff current | | I_{EBO} | $V_{CB} = 6 \text{ V}, I_{C} = 0$ | | | 100 | μΑ |
| Collector to emitter | 2SD1273 | V _{CEO} | $I_C = 25 \text{ mA}, I_B = 0$ | 60 | | | V |
| voltage | 2SD1273A | | Χ, | 80 | | | |
| Forward current transfe | er ratio * | h _{FE} | $V_{CE} = 4 \text{ V}, I_{C} = 0.5 \text{ A}$ | 500 | | 2 500 | |
| Collector to emitter saturation voltage | | V _{CE(sat)} | $I_C = 2 \text{ A}, I_B = 0.05 \text{ A}$ | | | 1 | V |
| Transition frequency | | f_T | $V_{CE} = 12 \text{ V}, I_C = 0.2 \text{ A}, f = 10 \text{ MHz}$ | | 50 | | MHz |

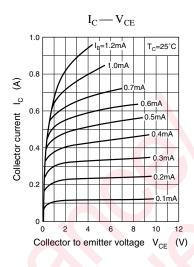
Note) *: Rank classification

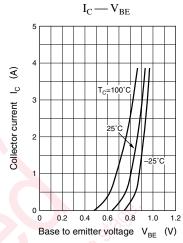
| Rank | Q | Р | 0 | |
|----------|--------------|--------------|----------------|--|
| h_{FE} | 500 to 1 000 | 800 to 1 500 | 1 200 to 2 500 | |

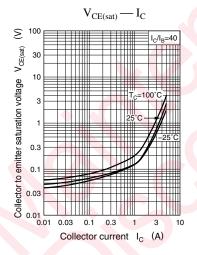
Ordering can be made by the common rank (PQ rank h_{FE} = 500 to 1 500) in the rank classification.

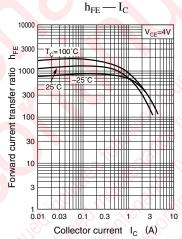
Panasonic 1

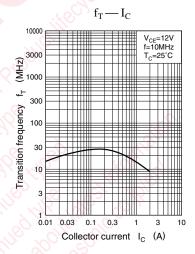


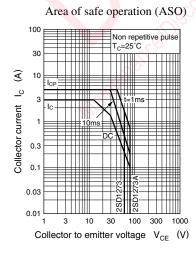


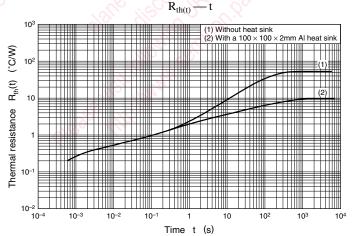












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